Features：

- Isolated mounting base 4000V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- Various rectifiers
- DC supply for PWM inverter

V_{DSM},V_{RSM}	V_{DRM},V_{RRM}	品名
2700V	2600V	Mx250D260C
2900V	2800V	Mx250D280C
3100V	3000V	Mx250D300C
3300V	3200V	Mx250D300C
3500V	3400V	Mx250D340C
3700V	3600V	Mx250D360C

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min.	Typ.	Max.	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, T_C=100°C	150			250	A
$I_{F(RMS)}$	RMS forward current					393	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			25	mA
I_{FSM}	Surge forward current	V_R=60%V_{RRM}, t=10ms half sine	150			9.5	kA
I^2t	I^2t for fusing coordination					451	10^3A^2s
V_{FO}	Threshold voltage		150			0.95	V
r_F	Forward slope resistance					0.87	mΩ
V_{FM}	Peak forward voltage	I_{FM}=750A	25			1.76	V
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C. Single side cooled per chip				0.13	°C/W
$R_{th(c-h)}$	Thermal resistance case to heatsink	D.C. Single side cooled per chip				0.04	°C/W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I_{iso}:1mA(MAX)		4000			V
F_m	Terminal connection torque(M8)			10.0		12.0	N·m
	Mounting torque(M6)			4.5		6.0	N·m
T_{vj}	Junction temperature			-40		150	°C
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight				680		g
Outline	M03						

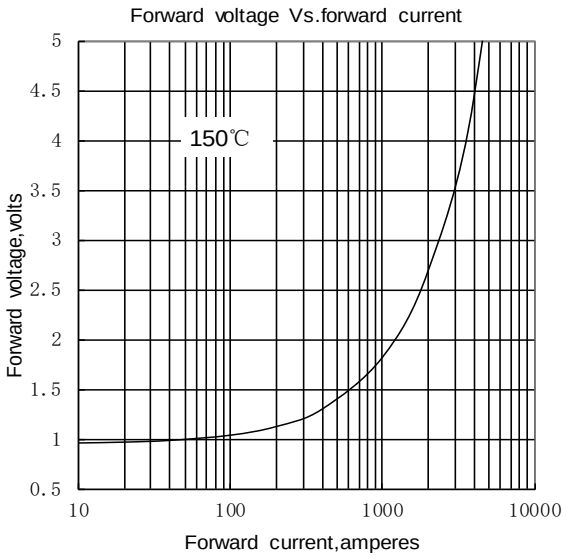


Fig.1

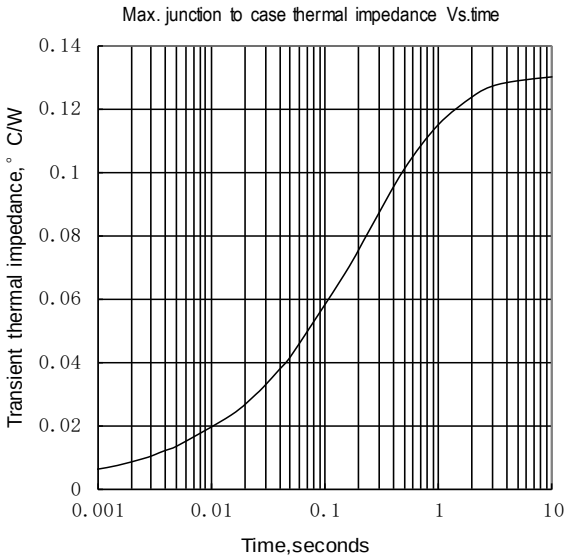


Fig.2

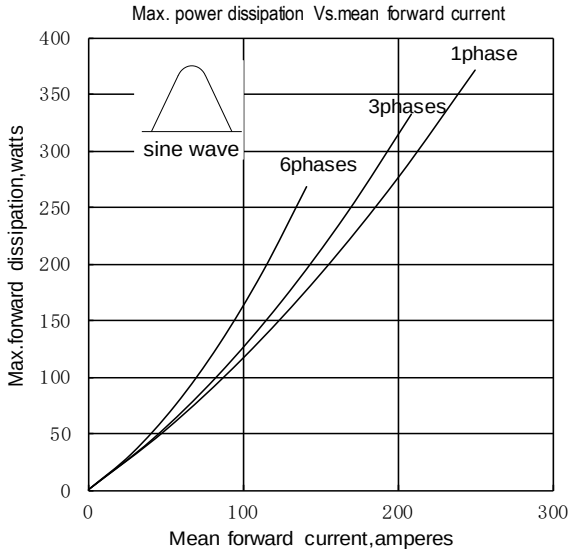


Fig.3

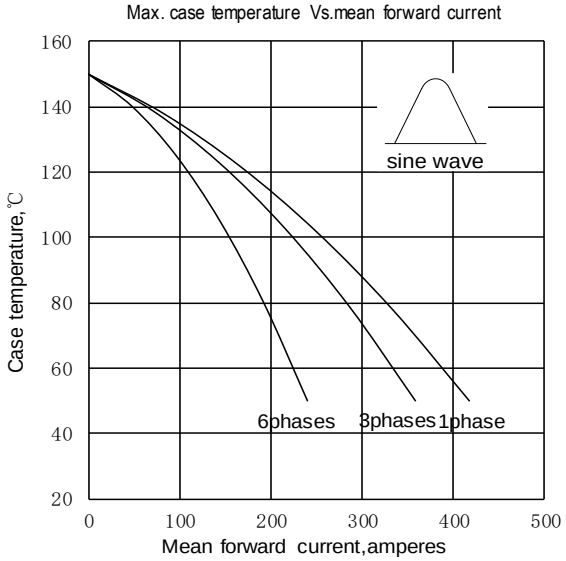


Fig.4

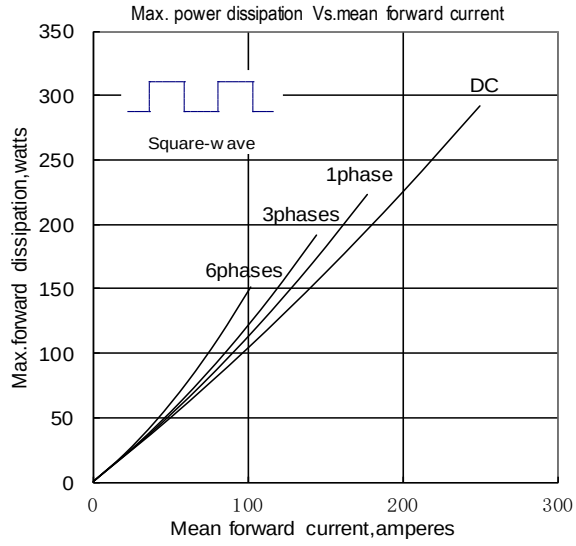


Fig.5

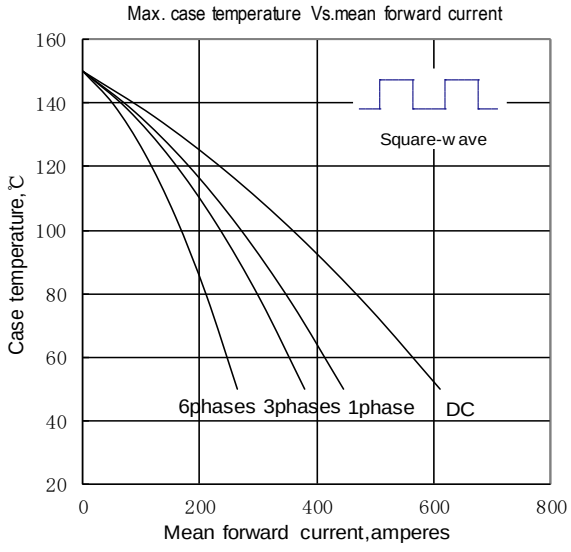


Fig.6

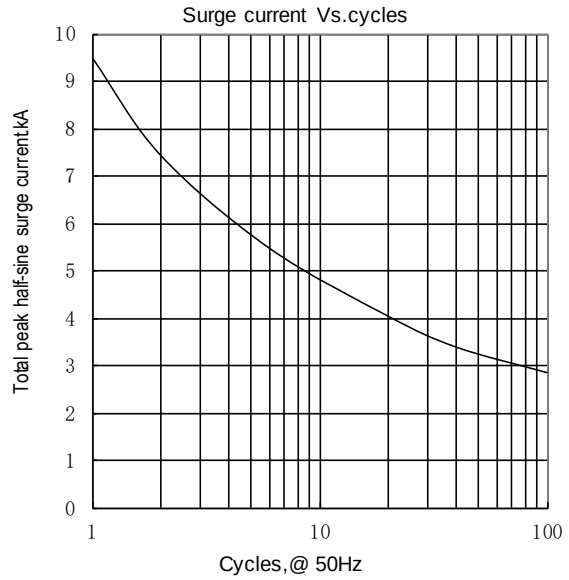
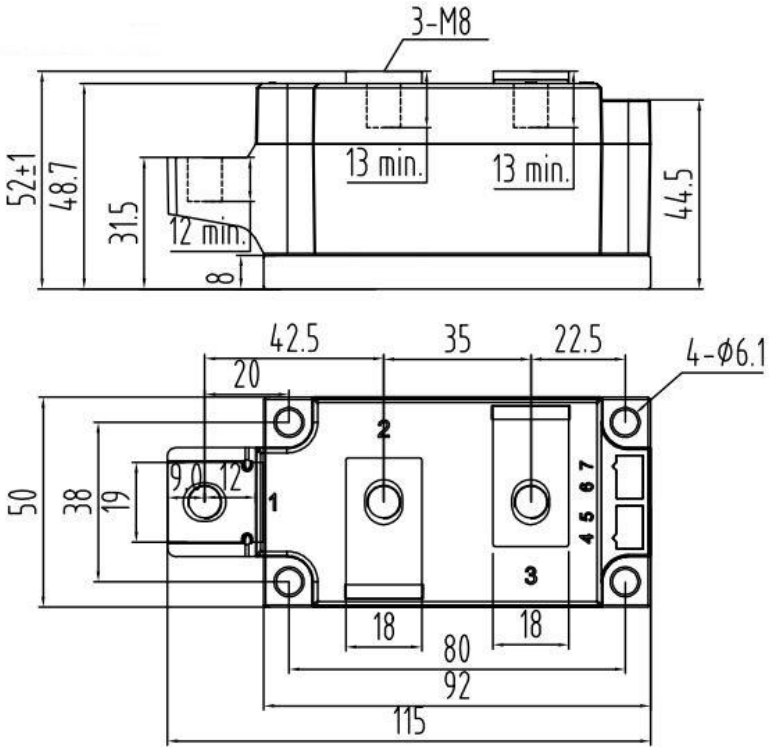
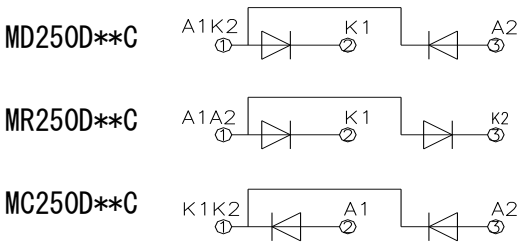


Fig.7





Unmarked dimensional tolerance：±0.5mm

NIps reserves the right to change specifications without notice.